

Shin-Ichi Kanemaru

List of Publications by Year in descending order

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141
papers

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279798

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142
all docs

142
docs citations

142
times ranked

1028
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Demonstration, Analysis, and Device Design Considerations for Independent DG MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 2046-2053. | 3.0 | 115 |
| 2 | Highly suppressed short-channel effects in ultrathin SOI n-MOSFETs. IEEE Transactions on Electron Devices, 2000, 47, 354-359. | 3.0 | 103 |
| 3 | Fabrication of double-gated Si field emitter arrays for focused electron beam generation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1968. | 1.6 | 99 |
| 4 | Destiny of Autologous Bone Marrow-Derived Stromal Cells Implanted in the Vocal Fold. Annals of Otolaryngology, Rhinology and Laryngology, 2005, 114, 907-912. | 1.1 | 78 |
| 5 | Emission statistics for Si and HfC emitter arrays after residual gas exposure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 707. | 1.6 | 73 |
| 6 | Fabrication and characterization of HfC coated Si field emitter arrays. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1589. | 1.6 | 51 |
| 7 | Ultrathin Channel Vertical DG MOSFET Fabricated by Using Ion-Bombardment-Retarded Etching. IEEE Transactions on Electron Devices, 2004, 51, 2078-2085. | 3.0 | 50 |
| 8 | Ultrastable emission from a metal-oxide-semiconductor field-effect transistor-structured Si emitter tip. Applied Physics Letters, 1996, 69, 1577-1578. | 3.3 | 49 |
| 9 | Control of emission currents from silicon field emitter arrays using a built-in MOSFET. Applied Surface Science, 1997, 111, 218-223. | 6.1 | 46 |
| 10 | Air-bridge-structured silicon nanowire and anomalous conductivity. Applied Physics Letters, 1999, 75, 3986-3988. | 3.3 | 39 |
| 11 | Control of emission characteristics of silicon field emitter arrays by an ion implantation technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1885. | 1.6 | 37 |
| 12 | Fabrication and characterization of lateral field-emitter triodes. IEEE Transactions on Electron Devices, 1991, 38, 2334-2336. | 3.0 | 35 |
| 13 | Fabrication of a New Si Field Emitter Tip with Metal-Oxide-Semiconductor Field-Effect Transistor (MOSFET) Structure. Japanese Journal of Applied Physics, 1996, 35, 6637-6640. | 1.5 | 34 |
| 14 | A New Metal-Oxide-Semiconductor Field-Effect-Transistor-Structured Si Field Emitter Tip. Japanese Journal of Applied Physics, 1996, 35, L861-L863. | 1.5 | 31 |
| 15 | Fabrication of Silicon Field Emitter Arrays Integrated with Beam Focusing Lens. Japanese Journal of Applied Physics, 1996, 35, 6626-6628. | 1.5 | 30 |
| 16 | Beam focusing characteristics of silicon microtips with an in-plane lens. IEEE Transactions on Electron Devices, 1997, 44, 498-502. | 3.0 | 30 |
| 17 | Emission Characteristics of Ion-Implanted Silicon Emitter Tips. Japanese Journal of Applied Physics, 1995, 34, 6907-6911. | 1.5 | 29 |
| 18 | A novel heteroepitaxy method of Ge films on CaF ₂ by electron beam exposure. Journal of Applied Physics, 1988, 63, 1060-1064. | 2.5 | 27 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Modeling of field emission nanotriodes with carbon nanotube emitters. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 366. | 1.6 | 27 |
| 20 | Fabrication of a Field Emitter Array with a Built-in Einzel Lens. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 06FK02. | 1.5 | 26 |
| 21 | The efficacy of a novel collagen-gelatin scaffold with basic fibroblast growth factor for the treatment of vocal fold scar. <i>Journal of Tissue Engineering and Regenerative Medicine</i> , 2017, 11, 1598-1609. | 2.7 | 26 |
| 22 | Regeneration of Mastoid Air Cells in Clinical Applications by In Situ Tissue Engineering. <i>Laryngoscope</i> , 2005, 115, 253-258. | 2.0 | 25 |
| 23 | Emission current saturation of the p-type silicon gated field emitter array. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 3357. | 1.6 | 24 |
| 24 | Fabrication of Si field emitter arrays integrated with metal-oxide-semiconductor field-effect transistor driving circuits. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 2309. | 1.6 | 24 |
| 25 | Electron-beam characteristics of double-gated Si field emitter arrays. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 1902. | 1.6 | 23 |
| 26 | Stable emission from a MOSFET-structured emitter tip in poor vacuum. <i>Applied Surface Science</i> , 1999, 146, 198-202. | 6.1 | 23 |
| 27 | A case of floppy epiglottis in adult: A simple surgical remedy. <i>Auris Nasus Larynx</i> , 2007, 34, 409-411. | 1.2 | 23 |
| 28 | Biocompatibility and Efficacy of Collagen/Gelatin Sponge Scaffold With Sustained Release of Basic Fibroblast Growth Factor on Vocal Fold Fibroblasts in 3-Dimensional Culture. <i>Annals of Otology, Rhinology and Laryngology</i> , 2015, 124, 116-125. | 1.1 | 23 |
| 29 | Fabrication of Volcano-Structured Double-Gate Field Emitter Array by Etch-Back Technique. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 5252-5255. | 1.5 | 22 |
| 30 | Fabrication of an ultrasharp and high-aspect-ratio microprobe with a silicon-on-insulator wafer for scanning force microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995, 13, 331. | 1.6 | 21 |
| 31 | Emission and focusing characteristics of volcano-structured double-gated field emitter arrays. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 701-704. | 1.3 | 21 |
| 32 | Characterization of electrical conduction in silicon nanowire by scanning Maxwell-stress microscopy. <i>Applied Physics Letters</i> , 2001, 78, 2560-2562. | 3.3 | 20 |
| 33 | Room-temperature crystallization of amorphous films by RF plasma treatment. <i>Thin Solid Films</i> , 2009, 517, 3092-3095. | 1.8 | 20 |
| 34 | Fabrication and Characterization of Comb-Shaped Lateral Field-Emitter Arrays. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 1221-1226. | 1.5 | 19 |
| 35 | Fabrication of a Nanometer-Scale Si-Wire by Micromachining of a Silicon-on-Insulator Substrate. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 7182-7185. | 1.5 | 19 |
| 36 | Fabrication and characterization of a nanogap edge emitter with a silicon-on-insulator wafer. <i>Applied Surface Science</i> , 1999, 146, 203-208. | 6.1 | 19 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 37 | Modeling of Optimized Field Emission Nanotriodes with Aligned Carbon Nanotubes of Variable Heights. Japanese Journal of Applied Physics, 2004, 43, 485-491. | 1.5 | 18 |
| 38 | HfC field emitter array controlled by built-in poly-Si thin film transistor. Journal of Vacuum Science & Technology B, 2006, 24, 936. | 1.3 | 18 |
| 39 | Fabrication of Si Field Emitter Tip for a Three-Dimensional Vacuum Magnetic Sensor. Japanese Journal of Applied Physics, 1996, 35, 6629-6631. | 1.5 | 17 |
| 40 | Fabrication of Metal-Oxide-Semiconductor Field-Effect-Transistor-Structured Silicon Field Emitters with a Polysilicon Dual Gate. Japanese Journal of Applied Physics, 1997, 36, 7736-7740. | 1.5 | 17 |
| 41 | Emission uniformity improvement of Si field emitter arrays by surface modification. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1581. | 1.6 | 17 |
| 42 | Microscopic characterization of field emitter array structure and work function by scanning Maxwell-stress microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2105. | 1.6 | 16 |
| 43 | Focusing Characteristics of Double-Gated Field-Emitter Arrays with a Lower Height of the Focusing Electrode. Applied Physics Express, 0, 1, 053001. | 2.4 | 16 |
| 44 | Low-voltage operation from the tower structure metal-oxide-semiconductor field-effect transistor Si field emitter. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 588. | 1.6 | 15 |
| 45 | Fabrication of Polycrystalline Silicon Field Emitter Arrays with Hafnium Carbide Coating for Thin-Film-Transistor Controlled Field Emission Displays. Japanese Journal of Applied Physics, 2004, 43, 3919-3922. | 1.5 | 15 |
| 46 | Characterization of enhanced field emission from HfC-coated Si emitter arrays through parameter extraction. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1227. | 1.6 | 15 |
| 47 | Characteristics of Ion-Induced Bending Phenomenon. Japanese Journal of Applied Physics, 2010, 49, 056501. | 1.5 | 15 |
| 48 | Improvement of the quality of Ge films on CaF ₂ /Si(111) structures by predeposited thin Ge layers. Surface Science, 1986, 174, 666-670. | 1.9 | 14 |
| 49 | Effects of conduction type on field-electron emission from single Si emitter tips with extraction gate. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1111. | 1.6 | 14 |
| 50 | Model parameter extraction for nonlinear Fowler-Nordheim field emission data. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1550. | 1.6 | 14 |
| 51 | Development of Thin-Film Bending Technique Induced by Ion-Beam Irradiation. Applied Physics Express, 2009, 2, 066501. | 2.4 | 14 |
| 52 | Three-dimensional vacuum magnetic sensor with a Si emitter tip. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1233. | 1.6 | 13 |
| 53 | Damageless vacuum sealing of Si field emitters with CHF ₃ plasma treatment. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 920. | 1.6 | 13 |
| 54 | Fabrication of ultrathin Si Channel Wall For Vertical Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor (DG MOSFET) by Using Ion-Bombardment-Retarded Etching (IBRE). Japanese Journal of Applied Physics, 2003, 42, 1916-1918. | 1.5 | 13 |

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| 55 | Control of Crystal Orientations in Lattice-Mismatched SrF ₂ and (Ca, Sr)F ₂ Films on Si Substrates by Intermediate CaF ₂ Films. Japanese Journal of Applied Physics, 1985, 24, L56-L58. | 1.5 | 12 |
| 56 | Suppressed threshold voltage roll-off characteristic of 40 nm gate length ultrathin SOI MOSFET. Electronics Letters, 1998, 34, 2069. | 1.0 | 12 |
| 57 | Work function controllability of metal gates made by interdiffusing metal stacks with low and high work functions. Microelectronic Engineering, 2005, 80, 284-287. | 2.4 | 12 |
| 58 | Silicon field emission array as novel charge neutralization device for high current ion implanter. Nuclear Instruments & Methods in Physics Research B, 2005, 237, 390-394. | 1.4 | 12 |
| 59 | A Novel Electron-Beam Exposure Epitaxy for Growing GaAs Films on Fluoride/Si Structures. Japanese Journal of Applied Physics, 1987, 26, L1834-L1836. | 1.5 | 11 |
| 60 | Single electron memory characteristic of silicon nanodot nanowire transistor. Electronics Letters, 2000, 36, 1322. | 1.0 | 11 |
| 61 | Individual tip evaluation in Si field emitter arrays by electrostatic lens projector. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 952. | 1.6 | 11 |
| 62 | Field emitter array with a memory function for ultrahigh luminance field emission display. Journal of Vacuum Science & Technology B, 2007, 25, 464. | 1.3 | 11 |
| 63 | Ring-shaped images as a result of nonuniform field emission from capped carbon nanotubes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 649. | 1.6 | 10 |
| 64 | Low-Operation-Voltage Comb-Shaped Field Emitter Array. Japanese Journal of Applied Physics, 1992, 31, L884-L886. | 1.5 | 9 |
| 65 | Vacuum Microtriode with Comb-Shaped Lateral Field-Emitter Array. Japanese Journal of Applied Physics, 1993, 32, L809-L812. | 1.5 | 9 |
| 66 | Electrical Characteristics of Air-Bridge-Structured Silicon Nanowire Fabricated by Micromachining a Silicon-on-Insulator Substrate. Japanese Journal of Applied Physics, 1999, 38, 7237-7240. | 1.5 | 9 |
| 67 | Optimization of transistor structure for transistor-stabilized field emitter arrays. IEEE Transactions on Electron Devices, 1999, 46, 2261-2264. | 3.0 | 9 |
| 68 | Emission-uniformity improvement and work-function reduction of Si emitter tips by ethylene gas exposure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1911. | 1.6 | 9 |
| 69 | Regeneration of mastoid air cells: Clinical applications. Acta Oto-Laryngologica, 2004, 124, 80-84. | 0.9 | 9 |
| 70 | Work function uniformity of Al-Ni alloys obtained by scanning Maxwell-stress microscopy as an effective tool for evaluating metal transistor gates. Applied Physics Letters, 2005, 86, 094104. | 3.3 | 9 |
| 71 | Fabrication and characterization of vertical-type, self-aligned asymmetric double-gate metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2005, 86, 123512. | 3.3 | 9 |
| 72 | A case report of myasthenia gravis localized to the larynx. Auris Nasus Larynx, 2007, 34, 401-403. | 1.2 | 9 |

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|----|---|-----|-----------|
| 73 | A field emitter array with an amorphous silicon thin-film transistor on glass. Applied Physics Letters, 1998, 73, 1301-1303. | 3.3 | 8 |
| 74 | A field emitter array monolithically integrated with a thin-film transistor on glass for display applications. Applied Surface Science, 1999, 146, 187-192. | 6.1 | 8 |
| 75 | Fabrication of a vacuum-sealed magnetic sensor with a Si field emitter tip. Journal of Micromechanics and Microengineering, 2001, 11, 81-83. | 2.6 | 8 |
| 76 | Dual-Gate Electron Emission Structure with Nanotube-on-Emitter for X-Ray Generation. Japanese Journal of Applied Physics, 2002, 41, 5551-5556. | 1.5 | 8 |
| 77 | CdTe x-ray image sensor using a field emitter array. Journal of Vacuum Science & Technology B, 2009, 27, 725-728. | 1.3 | 8 |
| 78 | Fabrication of a Three-Dimensional Vacuum Magnetic Sensor with a Si Tip. Japanese Journal of Applied Physics, 1997, 36, 7754-7756. | 1.5 | 7 |
| 79 | CHF3 Plasma Treatment of Si Field Emitter Arrays For No Damage Vacuum Packaging. Japanese Journal of Applied Physics, 2000, 39, L755-L756. | 1.5 | 7 |
| 80 | Novel Process for Vertical Double-Gate (DG) Metal-Oxide-Semiconductor Field-Effect-Transistor (MOSFET) Fabrication. Japanese Journal of Applied Physics, 2003, 42, 4138-4141. | 1.5 | 7 |
| 81 | Tissue engineering for the regeneration of the mastoid air cells: A preliminary in vitro study. Acta Oto-Laryngologica, 2004, 124, 75-79. | 0.9 | 7 |
| 82 | Scanning tunneling microscopy observations of hafnium carbide thin films as a field emission material. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 741. | 1.6 | 7 |
| 83 | Growth and Characterization of Compositionally Graded (Ca, Sr)F ₂ Layers on Si(111) Substrates. Japanese Journal of Applied Physics, 1987, 26, 848-851. | 1.5 | 6 |
| 84 | Amorphous-silicon-on-glass field emitter arrays. IEEE Electron Device Letters, 1996, 17, 261-263. | 3.9 | 6 |
| 85 | Modeling of Focused Carbon Nanotube Array Emitters for Field-Emission Displays. Japanese Journal of Applied Physics, 2004, 43, 3328-3334. | 1.5 | 6 |
| 86 | Diagnostics of doping integrity in n ⁺ /p/n ⁺ transistor-channel structure by scanning nonlinear dielectric microscopy. Applied Physics Letters, 2004, 84, 3169-3171. | 3.3 | 6 |
| 87 | Fabrication of Silicon Field Emitter Arrays with 0.1- μ m-Diameter Gate by Focused Ion Beam Lithography. Japanese Journal of Applied Physics, 1995, 34, 6932-6934. | 1.5 | 5 |
| 88 | Fabrication of a New Field Emitter Array with a Built-in Thin-Film Transistor on Glass. Japanese Journal of Applied Physics, 1998, 37, 7134-7137. | 1.5 | 5 |
| 89 | Plane-view observation technique of silicon nanowires by transmission electron microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1897. | 1.6 | 5 |
| 90 | Fabrication of HfC-Coated Si Field Emitter Arrays with Built-in Poly-Si Thin-Film Transistor. Japanese Journal of Applied Physics, 2005, 44, 5740-5743. | 1.5 | 5 |

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| 91 | 5-Fluorouracil Ointment for the Treatment of Otitis Media With Effusion. <i>Laryngoscope</i> , 2007, 117, 215-219. | 2.0 | 5 |
| 92 | Regenerative Treatment for Soft Tissue Defects of the External Auditory Meatus. <i>Otology and Neurotology</i> , 2014, 35, 442-448. | 1.3 | 5 |
| 93 | Nanoscale Evaluation of Structure and Surface Potential of Gated Field Emitters by Scanning Maxwell-Stress Microscope. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6912. | 1.5 | 4 |
| 94 | A MOSFET-structured Si tip for stable emission current. , 0, , . | | 4 |
| 95 | Fabrication of Field Emitter Arrays with Hydrogenated Amorphous Silicon on Glass. <i>Japanese Journal of Applied Physics</i> , 1996, 35, 6620-6622. | 1.5 | 4 |
| 96 | Fabrication technology of ultrafine SiO ₂ masks and Si nanowires using oxidation of vertical sidewalls of a poly-Si layer. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999, 17, 77. | 1.6 | 4 |
| 97 | Improvement of electron emission characteristics of Si field emitter arrays by surface modification. <i>Applied Surface Science</i> , 1999, 146, 172-176. | 6.1 | 4 |
| 98 | Mechanism of Tungsten Plug Corrosion during Chemical Stripping Process: Scanning Maxwell-Stress Microscopy and Electrochemical Potentiometry Studies. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5108-5112. | 1.5 | 4 |
| 99 | Demonstration of threshold voltage control techniques for vertical-type 4-terminal double-gate MOSFETs (4T-DGFET). , 0, , . | | 4 |
| 100 | Parameter dispersion characterization for arrays of HfC-coated emitters on poly-Si substrate. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 1045. | 1.3 | 4 |
| 101 | Fabrication of Petal-Shaped Vertical Field Emitter Arrays. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6916-6921. | 1.5 | 3 |
| 102 | Fabrication of 40-nm Gate Length Ultrathin n-MOSFETs Using Epitaxial Layer Transfer SOI Wafers. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2492-2495. | 1.5 | 3 |
| 103 | Doping diagnosis by evaluation of the surface Fermi level using scanning Maxwell-stress microscopy. <i>Applied Physics Letters</i> , 2003, 82, 2166-2168. | 3.3 | 3 |
| 104 | Silicon nanowire with programmable conductivity analyzed by scanning Maxwell-stress microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 664. | 1.6 | 3 |
| 105 | Metal-oxide-semiconductor field-effect transistor-structured Si field emitter array with a built-in ring gate lens. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 495. | 1.6 | 3 |
| 106 | Stabilization technique for columella using trimmed autologous temporal fascia in type III and IV tympanoplasty – muffler method. <i>Acta Oto-Laryngologica</i> , 2007, 127, 44-46. | 0.9 | 3 |
| 107 | Nanoscale Evaluation of Structure and Surface Potential of Gated Field Emitters by Scanning Maxwell-Stress Microscope. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6912-6915. | 1.5 | 3 |
| 108 | A regenerative approach for partial tracheal defects, an in vivo canine model. <i>Inflammation and Regeneration</i> , 2007, 27, 570-574. | 3.7 | 3 |

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|-----|--|-----|-----------|
| 109 | Fabrication and Characterization of Cross-Edge-Structured Vertical Field Emitter Arrays. Japanese Journal of Applied Physics, 1994, 33, 7171-7175. | 1.5 | 2 |
| 110 | Charging Damage of Silicon-on-Insulator (SOI) Wafer Determined by Scanning Maxwell-Stress Microscopy. Japanese Journal of Applied Physics, 2001, 40, 2907-2910. | 1.5 | 2 |
| 111 | Electron Motion Three-Dimensional Confinement for Microelectronic Vacuum Gauges with Field Emitters. Japanese Journal of Applied Physics, 2001, 40, 2165-2172. | 1.5 | 2 |
| 112 | Close Observation of the Geometrical Features of an Ultranarrow Silicon Nanowire Device. Japanese Journal of Applied Physics, 2002, 41, 4419-4422. | 1.5 | 2 |
| 113 | P-Channel Vertical Double-Gate MOSFET Fabricated by Utilizing Ion-Bombardment-Retarded Etching Process. Japanese Journal of Applied Physics, 2004, 43, 2156-2159. | 1.5 | 2 |
| 114 | Emission Statistics for HfC Emitter Arrays after Residual Gas Exposure. Japanese Journal of Applied Physics, 2005, 44, 5959-5963. | 1.5 | 2 |
| 115 | Design and fabrication of an ultrahigh-luminance field-emission display. Journal of Vacuum Science & Technology B, 2009, 27, 740. | 1.3 | 2 |
| 116 | Enhancement of ion-induced bending phenomenon using a double-layered film for field emitter array fabrication. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C2C1-C2C4. | 1.2 | 2 |
| 117 | Integration of thin film transistors and vertical thin film field emitter arrays using ion-induced bending. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 032205. | 1.2 | 2 |
| 118 | Silicon films on insulator formation using lateral solid-phase epitaxy induced by focused ion beam. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2699. | 1.6 | 1 |
| 119 | Feasibility of Vacuum Microelectronics Voltage Comparator. Japanese Journal of Applied Physics, 1995, 34, 6219-6221. | 1.5 | 1 |
| 120 | Emission Characteristics of Amorphous Silicon Field Emitter Arrays Sealed in a Vacuum Package. Japanese Journal of Applied Physics, 1999, 38, 7213-7216. | 1.5 | 1 |
| 121 | Fabrication technology of Si nanodot nanowire memory transistors using an inorganic EB resist process. , 0, , . | | 1 |
| 122 | Oscillator Ionization Vacuum Gauge with Field Emitters. Japanese Journal of Applied Physics, 2002, 41, 5945-5950. | 1.5 | 1 |
| 123 | Programmable Conductivity of Silicon Nanowires with Side Gates by Surface Charging. Japanese Journal of Applied Physics, 2003, 42, 2422-2425. | 1.5 | 1 |
| 124 | Current Status of Vacuum Microelectronics. IEEJ Transactions on Fundamentals and Materials, 2003, 123, 425-428. | 0.2 | 1 |
| 125 | Development of a CdTe x-ray imaging device driven by a vertical thin film field emission array. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C2D22-C2D25. | 1.2 | 1 |
| 126 | Ion induced bending (IIB) phenomenon for 3-D structure fabrication. Surface and Coatings Technology, 2011, 206, 775-780. | 4.8 | 1 |

| # | ARTICLE | IF | CITATIONS |
|-----|--|-----|-----------|
| 127 | Monolithic integration of Si field emitter arrays with n-MOSFET circuits. , 0, , . | | 0 |
| 128 | Silicon nanowire memory using surface charging and its operation analysis by scanning Maxwell-stress microscopy (SMM). , 0, , . | | 0 |
| 129 | Electrical and geometrical properties of a Si quantum nanowire device fabricated by an inorganic EB resist process. , 0, , . | | 0 |
| 130 | Fabrication of Si FEA integrated with MOSFET driving circuits. , 0, , . | | 0 |
| 131 | Modeling of field emission nanotriodes with carbon nanotube emitters. , 0, , . | | 0 |
| 132 | Ring-shaped images as a result of non-uniform field emission from capped carbon nanotubes. , 0, , . | | 0 |
| 133 | Emission statistics for Si and HfC/Si emitter arrays after gas exposure. , 0, , . | | 0 |
| 134 | On the V_{th} controllability for 4-terminal double-gate MOSFETs. , 0, , . | | 0 |
| 135 | STM observations of hafnium carbide thin films as a field emission material. , 0, , . | | 0 |
| 136 | Low temperature fabrication of poly-Si FEA for display application. , 0, , . | | 0 |
| 137 | Work function control of metal gates by interdiffused Ni-Ta with high thermal stability. , 0, , . | | 0 |
| 138 | Doping integrity diagnostics of planar transistor channel structures by scanning nonlinear dielectric microscopy. Journal of Vacuum Science & Technology B, 2006, 24, 237. | 1.3 | 0 |
| 139 | Determination of the best conditions of scaffolds for tissue engineered canine skull regeneration. Laryngoscope, 2009, 119, S257. | 2.0 | 0 |
| 140 | 10.2: Integration of TFT and VTF-FEA using ion-induced bending. , 2010, , . | | 0 |
| 141 | Densification of spin-on-glass (SOC) film by RF plasma treatment. IOP Conference Series: Materials Science and Engineering, 2011, 18, 032007. | 0.6 | 0 |